

# RJP4002ASA

# Nch IGBT for Strobe Flash

REJ03G1473-0100 Rev.1.00 Oct 13, 2006

#### **Features**

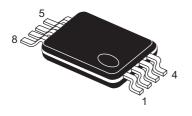
• Small surface mount package (TSSOP-8)

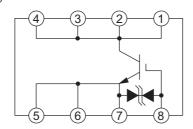
V<sub>CES</sub>: 400 VI<sub>CM</sub>: 150 A

• Drive voltage: 2.5 V

#### **Outline**

RENESAS Package code: PTSP0008JB-B (Package name: TSSOP-8 <TTP-8DV>)





1, 2, 3, 4 : Collector

5, 6 : Emitter 7 : Emitter

(for the gate drive)

8 : Gate

Note: Pin 7 is for the gate drive only.

Note that current from the main circuit cannot flow into this section. (Please see page 3.)

# **Applications**

Strobe flash for cameras

# **Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

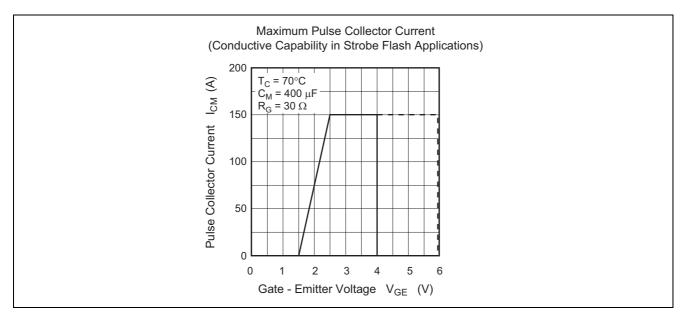
				(10 28 6)
Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V <sub>CES</sub>	400	V	V <sub>GE</sub> = 0 V
Gate-emitter voltage	$V_{GES}$	±4	V	V <sub>CE</sub> = 0 V
Peak gate-emitter voltage	$V_{GEM}$	±6	V	$V_{CE} = 0 \text{ V}, \text{ tw} = 10 \text{ s}$
Collector current (Pulse)	I <sub>CM</sub>	150	Α	$C_{M} = 400 \ \mu F$
				(see performance curve)
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	

## **Electrical Characteristics**

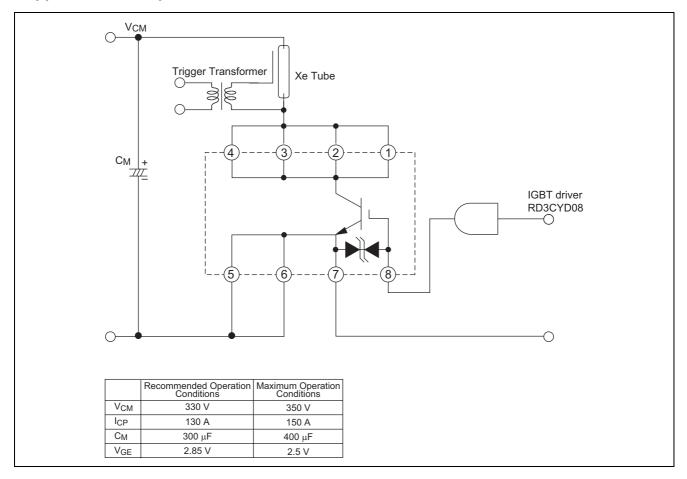
 $(Tj = 25^{\circ}C)$ 

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	$V_{(BR)CES}$	450	_	_	V	$I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$
Collector-emitter leakage current	I <sub>CES</sub>	_	_	10	μΑ	$V_{CE} = 400 \text{ V}, V_{GE} = 0 \text{ V}$
Gate-emitter leakage current	$I_{GES}$	_	_	±10	μΑ	$V_{GE} = \pm 4 \text{ V}, V_{CE} = 0 \text{ V}$
Gate-emitter threshold voltage	$V_{\text{GE(th)}}$	0.4	0.6	1.2	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	_	4.5	9.0	V	$I_C = 150 \text{ A}, V_{GE} = 2.5 \text{ V}$
Input capacitance	Cies	_	6500	_	pF	$V_{CE} = 25 \text{ V}, V_{GE} = 10 \text{ V},$
						f = 1MHz

## **Performance Curves**



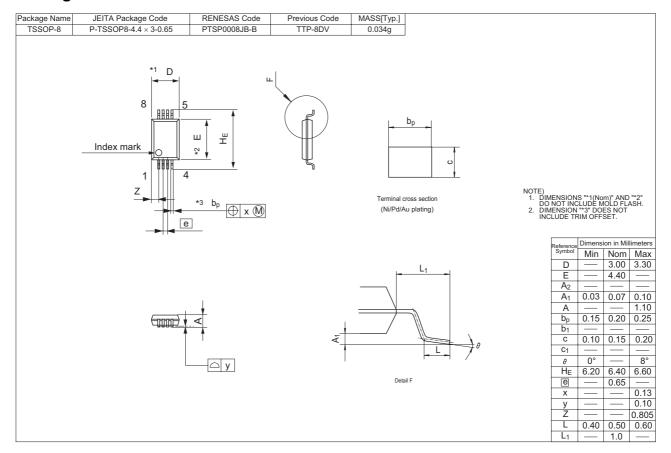
## **Application Example**



# **Precautions on Usage**

- 1. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 2. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And turn-off dv/dt must become less than 400 V/  $\mu s$ . In general, when  $R_{G\,(off)}$  = 30  $\Omega$ , it is satisfied.
- 3. The ground of the drive signal must be connected to pin 3 only. If the emitter terminal pins 1 and 2 in which a large currents flow are given to the device as the drive signal emitter, the device may be damaged due to large currents since the specified gate voltage is not applied to the IGBT within the device.
- 4. The operation life should be endured until repeated discharge of 5,000 times under the charge current ( $I_{Xe} \le 150 \text{ A}$ : full luminescence condition) of main capacitor. Repetition period under full luminescence condition is over 3 seconds
- 5. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours when V<sub>GE</sub> is driven at 4 V.

## **Package Dimensions**



#### **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example	
Surface-mounted type	Taping	3000	Type name - 00 - Q0	RJP4002ASA-00-Q0	

Note: Please confirm the specification about the shipping in detail.

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- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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